

## UNISONIC TECHNOLOGIES CO., LTD

UT3310 Preliminary Power MOSFET

# P-CHANNEL ENHANCEMENT MODE POWER MOSFET

#### ■ DESCRIPTION

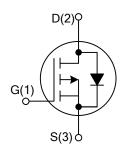
The UTC **UT3310** is a P-channel enhancement mode Power MOSFET. The UTC **UT3310** uses advanced technology to provide customers with fast switching, low on-resistance and cost-effectiveness.

The UTC **UT3310** is generally applied in low voltage and battery power applications.

#### ■ FEATURES

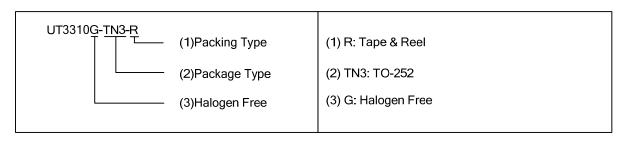
- \* Gate Drive Capability: 2.5V
- \* Simple Drive Requirement

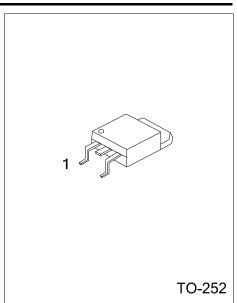
#### ■ SYMBOL



#### ■ ORDERING INFORMATION

|  | Ordering Number | Package | Pin Assignment |   |   | Packing   |  |
|--|-----------------|---------|----------------|---|---|-----------|--|
|  |                 |         | 1              | 2 | 3 | Packing   |  |
|  | UT3310G-TN3-R   | TO-252  | G              | D | S | Tape Reel |  |





#### ■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER   | SYMBOL           | RATINGS    | UNIT                 |
|---|------------------|------------|----------------------|
| Drain to Source Voltage   | V <sub>DSS</sub> | -20        | V                    |
| Gate to Source Voltage  | $V_{GSS}$        | ±12        | V                    |
| Continuous Drain Current (T <sub>A</sub> =25°C, V <sub>GS</sub> =10V) | I <sub>D</sub>   | -10        | Α                    |
| Pulsed Drain Current  | I <sub>DM</sub>  | -24        | Α                    |
| Total Power Dissipation (T <sub>A</sub> =25°C)                        | $P_{D}$          | 25         | W                    |
| Linear Derating Factor  |                  | 0.01       | W/°C                 |
| Junction Temperature  | TJ               | 150        | $^{\circ}\mathbb{C}$ |
| Ambient Operating Temperature   | T <sub>OPR</sub> | -55 ~ +150 | $^{\circ}\mathbb{C}$ |
| Storage Temperature   | T <sub>STG</sub> | -55 ~ +150 | $^{\circ}$           |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ THERMAL DATA

| PARAMETER           | SYMBOL        | RATINGS | UNIT |  |
|---------------------|---------------|---------|------|--|
| Junction to Ambient | $\theta_{JA}$ | 110     | °C/W |  |
| Junction to Case    | $\theta_{JC}$ | 5.0     | °C/W |  |

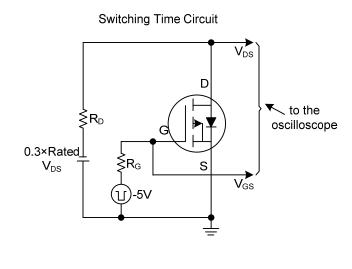
### ■ ELECTRICAL CHARACTERISTICS (T」=25°C, unless otherwise specified)

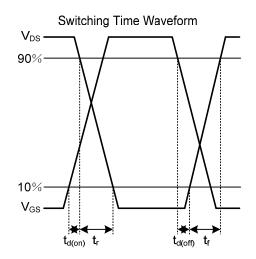
| PARAMETER                                 | SYMBOL                       | TEST CONDITIONS                                   | MIN  | TYP  | MAX  | UNIT |  |  |
|---|------------------------------|---|------|------|------|------|--|--|
| OFF CHARACTERISTICS                       |                              |   |      |      |      |      |  |  |
| Drain-Source Breakdown Voltage            | $BV_{DSS}$                   | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA       | -20  |      |      | V    |  |  |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_J$ | Reference to 25°C, I <sub>D</sub> =-1mA           |      | -0.1 |      | V/°C |  |  |
| Drain-Source Leakage Current              | $I_{DSS}$                    | $V_{DS}$ =-20V, $V_{GS}$ =0V                      |      |      | -1   | μΑ   |  |  |
| Gate-Source Leakage Current               | $I_{GSS}$                    | V <sub>DS</sub> =0V ,V <sub>GS</sub> =±12V        |      |      | ±100 | nA   |  |  |
| ON CHARACTERISTICS                        |                              |   |      |      |      |      |  |  |
| Gate Threshold Voltage                    | $V_{GS(TH)}$                 | $V_{DS} = V_{GS}$ , $I_D = -250 \mu A$            | -0.5 |      |      | V    |  |  |
| Drain-Source On-State Resistance          | R <sub>DS(ON)</sub>          | $V_{GS}$ =-4.5V, $I_{D}$ =-2.8A                   |      |      | 150  | mΩ   |  |  |
| Dialii-Source Oil-State Resistance        |                              | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A     |      |      | 250  | mΩ   |  |  |
| DYNAMIC PARAMETERS                        |                              |   |      |      |      |      |  |  |
| Input Capacitance                         | C <sub>ISS</sub>             |   |      | 300  |      | pF   |  |  |
| Output Capacitance                        | Coss                         | $V_{DS}$ =-6V, $V_{GS}$ =0V,f =1.0MHz             |      | 180  |      | pF   |  |  |
| Reverse Transfer Capacitance              | $C_{RSS}$                    |   |      | 60   |      | рF   |  |  |
| SWITCHING PARAMETERS                      |                              |   |      |      |      |      |  |  |
| Total Gate Charge (Note2)                 | $Q_G$                        |   |      | 6    |      | nC   |  |  |
| Gate-Source Charge                        | $Q_GS$                       | $V_{DS}$ =-6V, $V_{GS}$ =-5V, $I_{D}$ =-2.8A      |      | 1.5  |      | nC   |  |  |
| Gate-Drain Charge                         | $Q_GD$                       |   |      | 0.6  |      | nC   |  |  |
| Turn-ON Delay Time (Note2)                | $t_{D(ON)}$                  |   |      | 25   |      | ns   |  |  |
| Turn-ON Rise Time                         | $t_R$                        | $V_{DS}$ =-6V, $V_{GS}$ =-5V, $I_{D}$ =-1A        |      | 60   |      | ns   |  |  |
| Turn-OFF Delay Time                       | $t_{D(OFF)}$                 | $R_G=6\Omega$ , $R_D=6\Omega$                     |      | 70   |      | ns   |  |  |
| Turn-OFF Fall Time                        | t <sub>F</sub>               |   |      | 60   |      | ns   |  |  |
| SOURCE-DRAIN DIODE RATINGS AND CH         | IARACTERIS                   | TICS  |      |      | -    |      |  |  |
| Continuous Source Current ( Body Diode )  | Is                           | $V_D=V_G=0V$ , $V_S=-1.2V$                        |      |      | -10  | Α    |  |  |
| Pulsed Source Current ( Body Diode )      | I <sub>SM</sub>              | (Note1)   |      |      | -24  | Α    |  |  |
| Drain-Source Diode Forward Voltage        | $V_{SD}$                     | I <sub>S</sub> =-10A, V <sub>GS</sub> =0V (Note2) |      |      | -1.2 | V    |  |  |

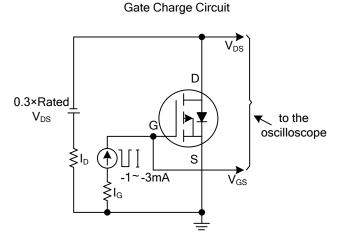
Notes:1. Pulse width limited by safe operating area.

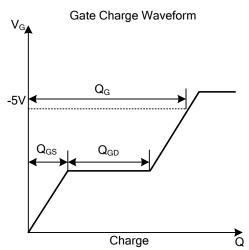
2. Pulse width ≤300us , duty cycle ≤2%.

#### ■ TYPICAL CHARACTERISTICS









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